

Notice of References Cited

Application/Control No.

09/944,981

Applicant(s)/Patent Under
Reexamination
AHN ET AL.

Examiner

Walter L. Lindsay, Jr.

Art Unit

2812

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	B	US-6,020,024	02-2000	Maiti et al.	438/287
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	M	US-			

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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Kwo et al., Properties of high K gate dielectrics Gd2O3 and Y2O3 for Si, 10/16/00, Journal of Applied Physics, Volume 89 No. 7 pp 3920-3927
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.